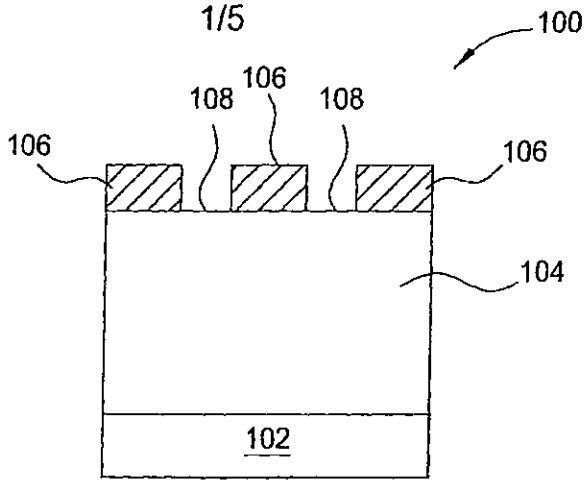


FIG. 1A
(PRIOR ART)

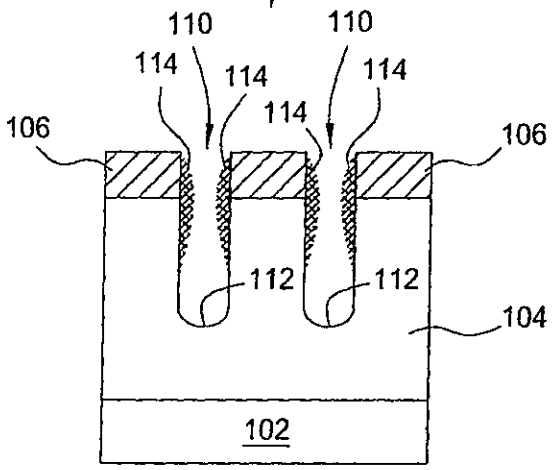


FIG. 1B
(PRIOR ART)

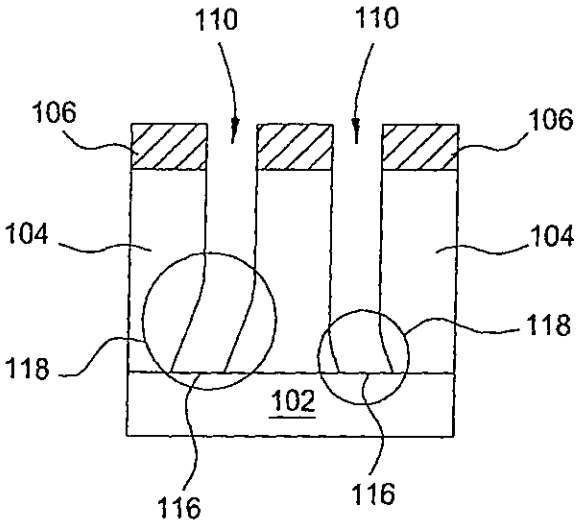


FIG. 1C
(PRIOR ART)

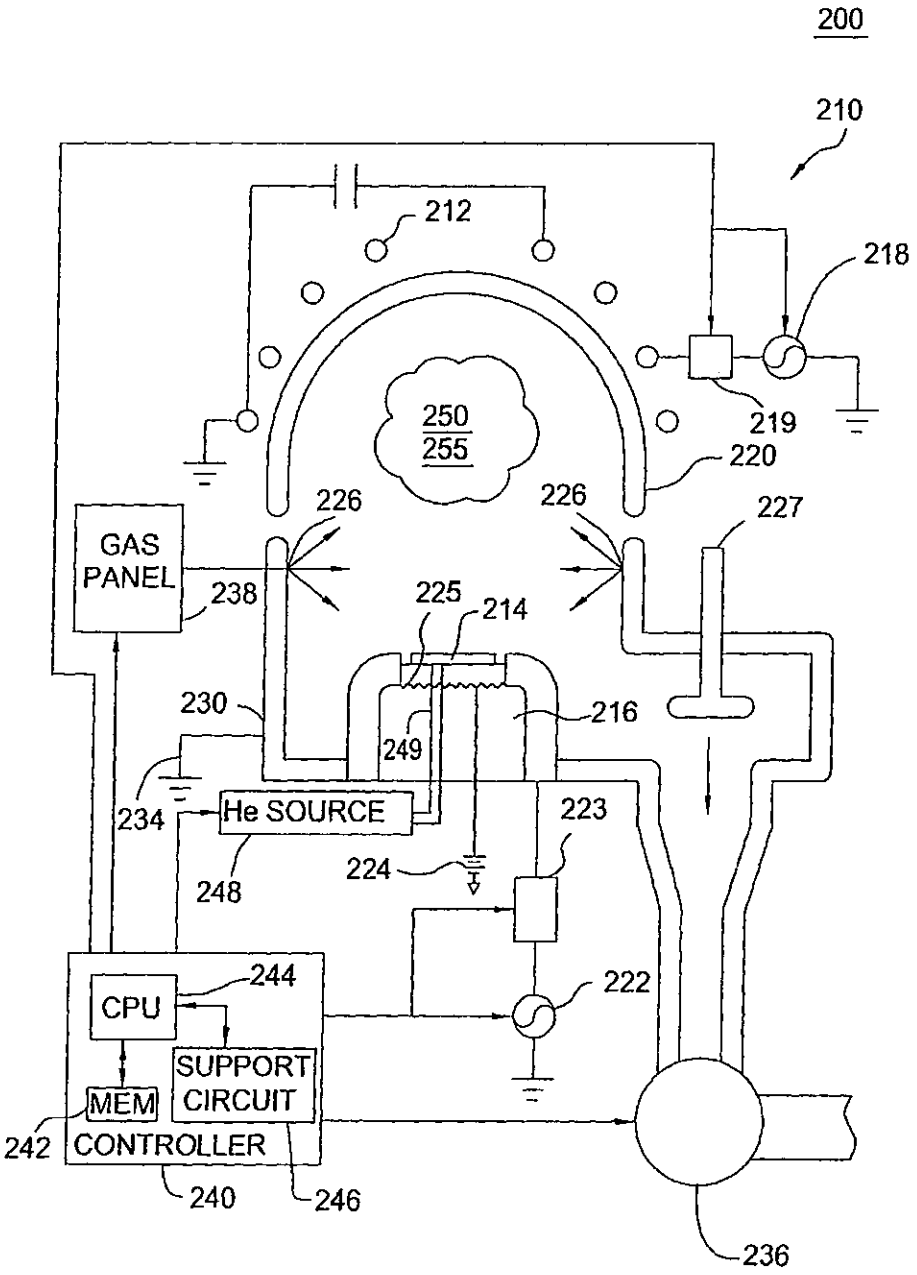

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255
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227
GAS
PANEL
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249
234
He SOURCE
223
224
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244
CPU
222
SUPPORT
CIRCUIT
MEM
242
CONTROLLER
240
246
236

FIG. 2

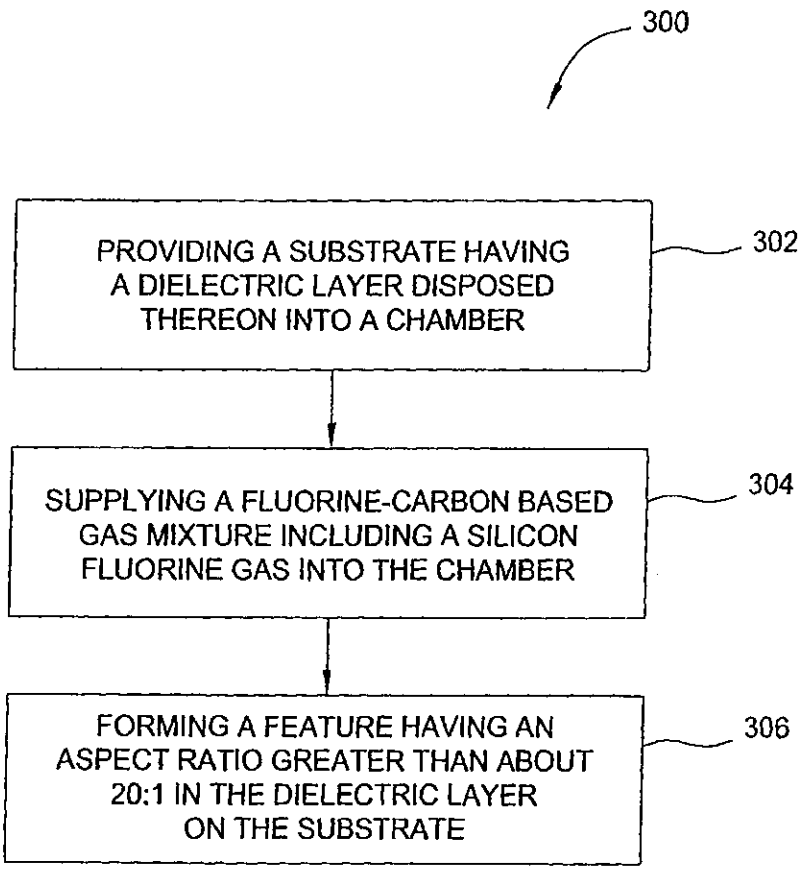

300
PROVIDING A SUBSTRATE HAVING A DIELECTRIC LAYER DISPOSED THEREON INTO A CHAMBER
302
SUPPLYING A FLUORINE-CARBON BASED GAS MIXTURE INCLUDING A SILICON FLUORINE GAS INTO THE CHAMBER
304
FORMING A FEATURE HAVING AN ASPECT RATIO GREATER THAN ABOUT 20:1 IN THE DIELECTRIC LAYER ON THE SUBSTRATE
306

FIG. 3

FIG. 4A

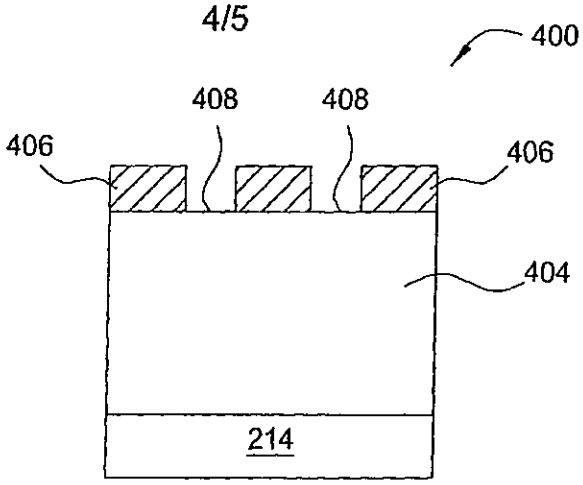


FIG. 4B

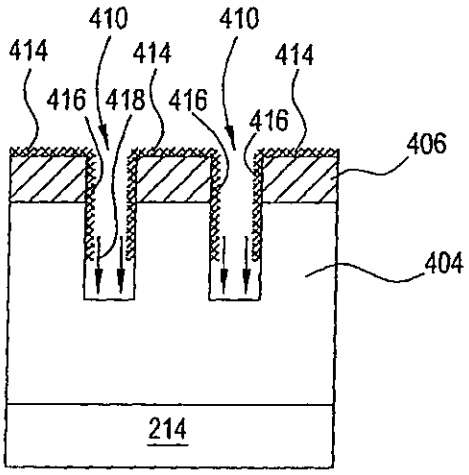
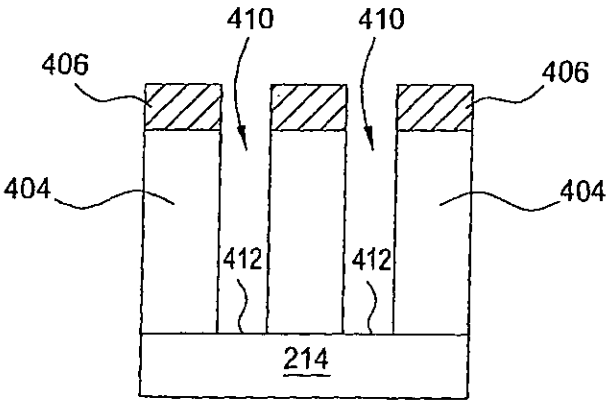


FIG. 4C



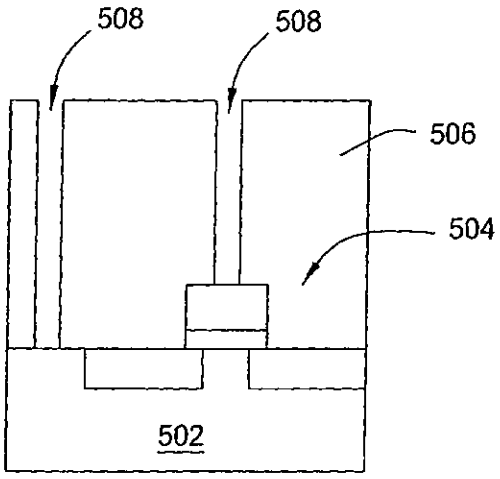


FIG. 5